

SMB1N-770D-02

- IR High-Power LED
- 770 nm, 650 mW
- AlGaInP chip, 1000 x 1000 μm
- PA9T SMD package
- Beam Angle: ± 10°



Description

SMB1N-770D-02 is a surface mount AlGaInP based high power infrared LED, with a typical peak wavelength of 770 nm and optical output power of 650 mW @ 800 mA. It comes in polyamide resin SMD package (PA9T) with silver plated soldering pads (lead free solderable), copper heat sink, and silicone resin molded lens. Additional variants with different beam angles are available on request.

Maximum Ratings*

| Parameter | Symbol | Va | Unit | |
|---|--------|------|-------|------|
| Farameter | Symbol | Min. | Max. | Unit |
| Power Dissipation | PD | | 2000 | mW |
| Forward Current | lF | | 800 | mA |
| Pulse Forward Current ** | IFP | | 2000 | mA |
| Reverse Voltage (I _R =10 µA) | UR | | 5 | V |
| Reverse Current (U _R =5 V) | IR | | 10 | μA |
| Thermal Resistance | Rthja | | 10 | K/W |
| Junction Temperature | TJ | | 120 | °C |
| Operating Temperature | TCASE | - 40 | + 100 | °C |
| Storage Temperature | Tstg | - 40 | + 100 | °C |
| Lead Solder Temperature (t _{max} . 5s) | TSLD | | + 250 | °C |

* Operating close to or exceeding these parameters may damage the device

** duty cycle = 1 %, pulse width = 10 μ s

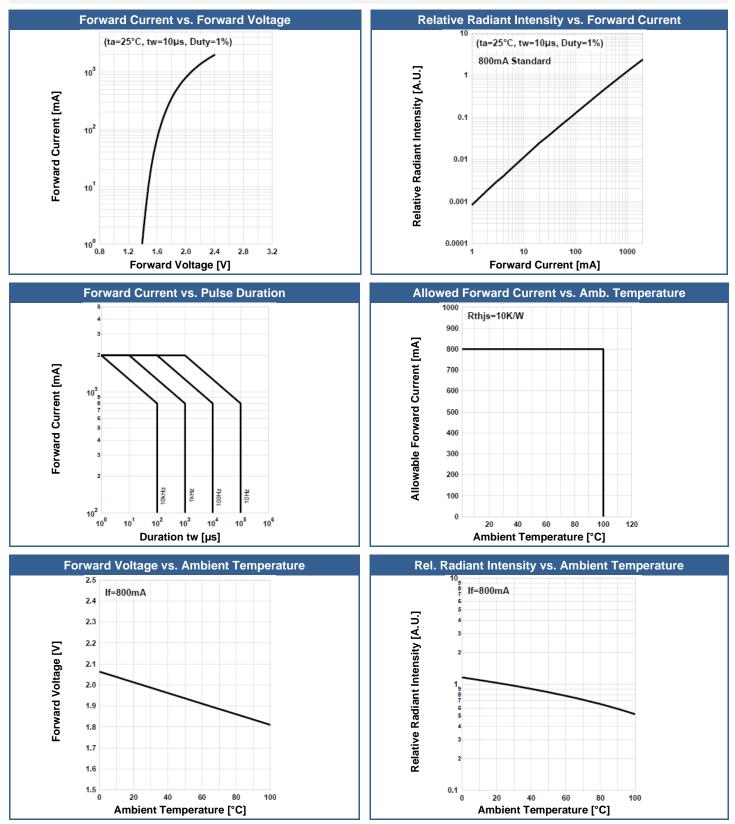
Electro-Optical Characteristics (TCASE = 25°C)

| Parameter | Symbol | Conditions | Min. | Values Typ. | Max. | Unit |
|----------------------|--------------------|------------------------|------|----------------|------|-------|
| Peak Wavelength | λP | I⊧=800 mA | 760 | | 780 | nm |
| Half Width | λ_{Δ} | I _F =800 mA | | 20 | | nm |
| Forward Voltage | UF | I _F =800 mA | | 2.1 | 2.5 | V |
| | UFP | IFP=2 A | | 2.6 | | |
| Total Radiated Power | Po | I⊧=800 mA | 450 | 650 | | mW |
| | | IFP=2 A | | 1500 | | |
| Radiant Intensity | lE | I⊧=800 mA | | 1400 | | mW/sr |
| | | IFP=2 A | | 3200 | | |
| Viewing Angle | 20 1/2 | I _F =100 mA | | 20 | | deg. |
| Rise Time | tr | I _F =800 mA | | 45 | | ns |
| Fall Time | tr | I _F =800 mA | | 40 | | ns |

* duty cycle = 1 %, pulse width = 10 μs

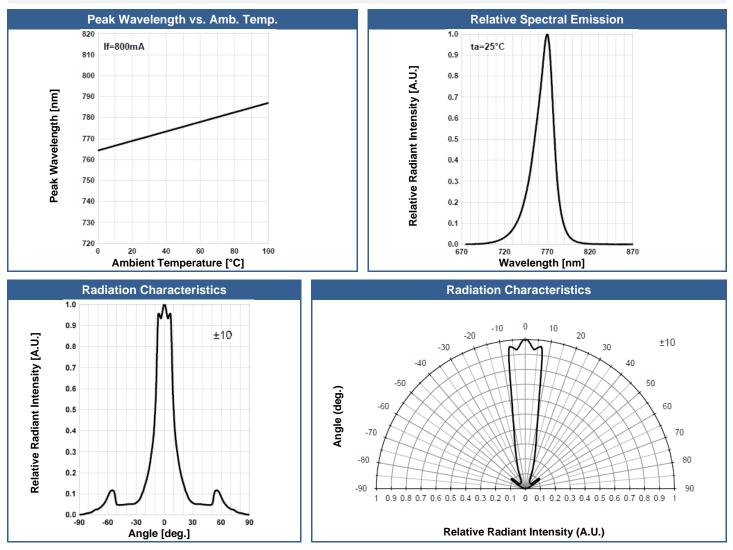


Typical Performance Curves

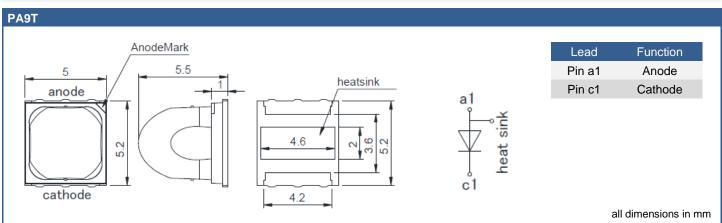




Typical Performance Curves



Outline Dimensions

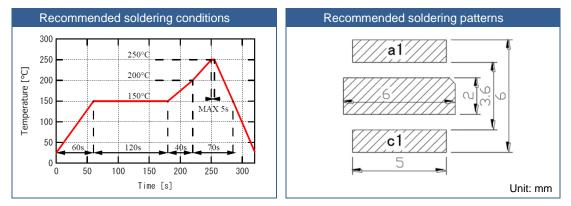




General Notes

Soldering

- Do avoid overheating of the LED
- Do avoid electrostatic discharge (ESD)
- Do avoid mechanical stress, shock, and vibration
- Do only use non-corrosive flux
- · Do not apply current to the LED until it has cooled down to room temperature after soldering



Cleaning

- · Cleaning with isopropyl alcohol, propanol, or ethyl alcohol is recommended
- DO NOT USE acetone, chloroseen, trichloroethylene, or MKS
- DO NOT USE ultrasonic cleaners

Static Electricity

- LEDs are sensitive to electrostatic discharge (ESD).
- · Precautions against ESD must be taken when handling or operating these LEDs
- · Surge voltage or electrostatic discharge can result in complete failure of the LED.

Radiation

- During operation these LEDs do emit light, which could be hazardous to skin and eyes, and may cause cancer.
- Do avoid exposure to the emitted light. Protective glasses if needed
- It is further advised to attach a warning label on products/systems.

Operation

- Do only operate LEDs with a current source.
- Running these LEDs from a voltage source will result in complete failure of the device.
- Current of a LED is an exponential function of the voltage across it. Usage of current regulated drive circuits is mandatory.

Storage

- The maximum shelf life of LEDs in the originally sealed aluminum bag is 12 months.
- Before opening the aluminum bag, please store it at <30 °C, <60 % RH.
- After opening the aluminum bag, please solder the LEDs within 72 hours (floor life) at 5 30 °C, <50 % RH.
- Put any unused, remaining LEDs and silica gel back in the same aluminum bag and then vacuum-seal the bag.
- It is recommended to keep the re-sealed bag in a desiccator at <30%RH.

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